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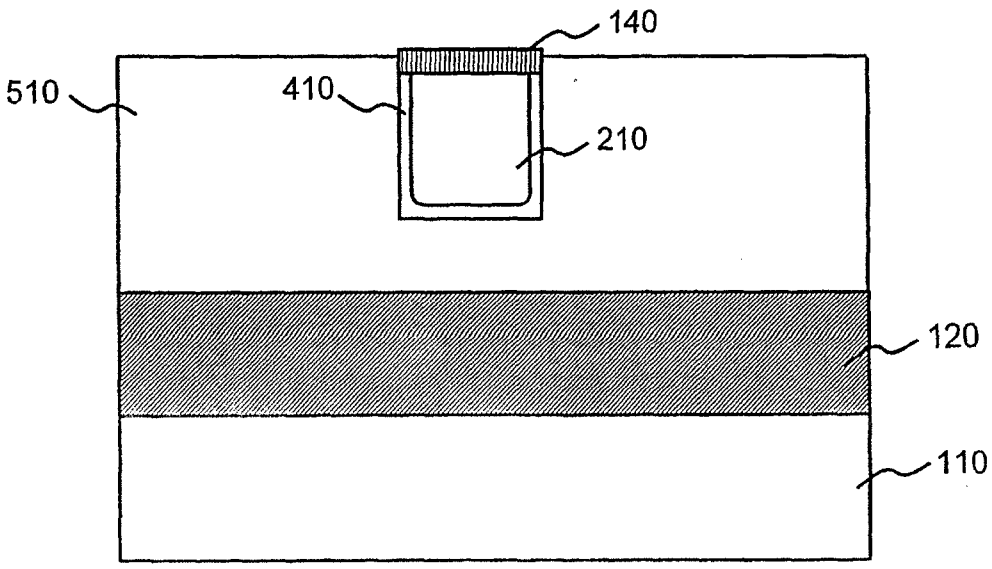
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(54) Title: SEMICONDUCTOR DEVICE HAVING A U-SHAPED GATE STRUCTURE



(57) Abstract: A double-gate semiconductor device (100) includes a substrate (110), an insulating layer (120), a fin (210) and agate (510). The insulating layer (120) is formed on the substrate (110) and the gate (510) is formed on the insulating layer (120). The fin (210) has a number of side surfaces, a top surface and a bottom surface. The bottom surface and at least a portion of the side surfaces of the fin (210) are surrounded by the gate (510). The gate material (510) surrounding the fin (210) has a U-shaped cross-section at a channel region of the semiconductor device (100).

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